Dongsuk Lim

List of Publications by Year
in descending order

11 papers	411 citations	1040056 9 h-index	1281871 11 g-index
11 all docs	11 docs citations	11 times ranked	966 citing authors

#	Article	IF	Citations
1	Tunable Electrical and Optical Characteristics in Monolayer Graphene and Few-Layer MoS₂ Heterostructure Devices. Nano Letters, 2015, 15, 5017-5024.	9.1	150
2	Gateâ€Tunable Hole and Electron Carrier Transport in Atomically Thin Dualâ€Channel WSe₂/MoS₂ Heterostructure for Ambipolar Fieldâ€Effect Transistors. Advanced Materials, 2016, 28, 9519-9525.	21.0	70
3	Electrical characterization of multilayer HfSe2 field-effect transistors on SiO2 substrate. Applied Physics Letters, 2015, 106, .	3.3	50
4	Tunable electrical properties of multilayer HfSe₂field effect transistors by oxygen plasma treatment. Nanoscale, 2017, 9, 1645-1652.	5.6	38
5	Observation of negative differential resistance in mesoscopic graphene oxide devices. Scientific Reports, 2018, 8, 7144.	3.3	25
6	Gate Tunable Self-Biased Diode Based on Few Layered MoS₂ and WSe₂. Chemistry of Materials, 2018, 30, 1011-1016.	6.7	20
7	Tunable Electron and Hole Injection Enabled by Atomically Thin Tunneling Layer for Improved Contact Resistance and Dual Channel Transport in MoS₂/WSe₂ van der Waals Heterostructure. ACS Applied Materials & Interfaces, 2018, 10, 23961-23967.	8.0	17
8	Photodetector Based on Multilayer SnSe₂ Field Effect Transistor. Journal of Nanoscience and Nanotechnology, 2018, 18, 4243-4247.	0.9	14
9	High performance MoS₂-based field-effect transistor enabled by hydrazine doping. Nanotechnology, 2016, 27, 225201.	2.6	11
10	P-doping and efficient carrier injection induced by graphene oxide for high performing WSe2 rectification devices. Applied Physics Letters, 2016, 108, .	3.3	8
11	Junctionless Diode Enabled by Self-Bias Effect of Ion Gel in Single-Layer MoS₂ Device. ACS Applied Materials & Interfaces, 2017, 9, 26983-26989.	8.0	8